

1N5333B Series

5 Watt Surmetic™ 40 Zener Voltage Regulators

This is a complete series of 5 Watt Zener diodes with tight limits and better operating characteristics that reflect the superior capabilities of silicon-oxide passivated junctions. All this in an axial-lead, transfer-molded plastic package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range – 3.3 V to 200 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Surge Rating of up to 180 W @ 8.3 ms
- Maximum Limits Guaranteed on up to Six Electrical Parameters

Mechanical Characteristics:

CASE: Void free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from the case for 10 seconds

POLARITY: Cathode indicated by polarity band

MOUNTING POSITION: Any

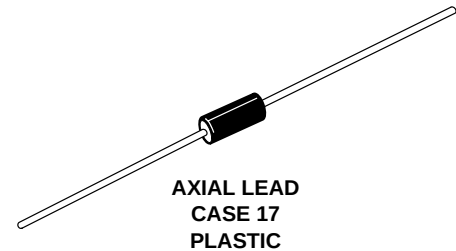
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ $T_L = 75^\circ\text{C}$, Lead Length = 3/8" Derate above 75°C	P_D	5 40	W mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +200	°C

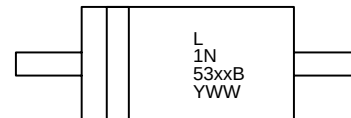


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MARKING DIAGRAM



L = Assembly Location
1N53xxB = Device Code
(See Table Next Page)
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
1N53xxB	Axial Lead	1000 Units/Box
1N53xxBRL	Axial Lead	4000/Tape & Reel
1N53xxBTA*	Axial Lead	2000/Ammo Pack

*1N5361B Not Available in 2000/Ammo Pack

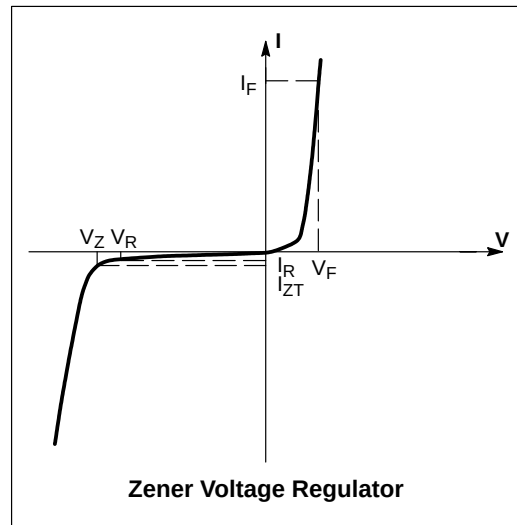
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Devices listed in **bold, italic** are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value.

1N5333B Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.2\text{ V Max @ } I_F = 1.0\text{ A}$ for all types)

Symbol	Parameter
V_Z	Reverse Zener Voltage @ I_{ZT}
I_{ZT}	Reverse Current
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}
I_R	Reverse Leakage Current @ V_R
V_R	Breakdown Voltage
I_F	Forward Current
V_F	Forward Voltage @ I_F
I_R	Maximum Surge Current @ $T_A = 25^\circ\text{C}$
ΔV_Z	Reverse Zener Voltage Change
I_{ZM}	Maximum DC Zener Current



1N5333B Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.2\text{ V Max}$ @ $I_F = 1.0\text{ A}$ for all types)

Device (Note 1)	Device Marking	Zener Voltage (Note 2)				Zener Impedance (Note 2)			Leakage Current		I _R (Note 3)	ΔV _Z (Note 4)	I _{ZM} (Note 5)
		V _Z (Volts)			@ I _{ZT}	Z _{TT} @ I _{ZT}	Z _{TK} @ I _{ZK}	I _{ZK}	I _R @ V _R				
		Min	Nom	Max	mA	Ω	Ω	mA	μA Max	Volts			
1N5333B	1N5333B	3.14	3.3	3.47	380	3	400	1	300	1	20	0.85	1440
1N5334B	1N5334B	3.42	3.6	3.78	350	2.5	500	1	150	1	18.7	0.8	1320
1N5335B	1N5335B	3.71	3.9	4.10	320	2	500	1	50	1	17.6	0.54	1220
1N5336B	1N5336B	4.09	4.3	4.52	290	2	500	1	10	1	16.4	0.49	1100
1N5337B	1N5337B	4.47	4.7	4.94	260	2	450	1	5	1	15.3	0.44	1010
1N5338B	1N5338B	4.85	5.1	5.36	240	1.5	400	1	1	1	14.4	0.39	930
1N5339B	1N5339B	5.32	5.6	5.88	220	1	400	1	1	2	13.4	0.25	865
1N5340B	1N5340B	5.70	6.0	6.30	200	1	300	1	1	3	12.7	0.19	790
1N5341B	1N5341B	5.89	6.2	6.51	200	1	200	1	1	3	12.4	0.1	765
1N5342B	1N5342B	6.46	6.8	7.14	175	1	200	1	10	5.2	11.5	0.15	700
1N5343B	1N5343B	7.13	7.5	7.88	175	1.5	200	1	10	5.7	10.7	0.15	630
1N5344B	1N5344B	7.79	8.2	8.61	150	1.5	200	1	10	6.2	10	0.2	580
1N5345B	1N5345B	8.27	8.7	9.14	150	2	200	1	10	6.6	9.5	0.2	545
1N5346B	1N5346B	8.65	9.1	9.56	150	2	150	1	7.5	6.9	9.2	0.22	520
1N5347B	1N5347B	9.50	10	10.5	125	2	125	1	5	7.6	8.6	0.22	475
1N5348B	1N5348B	10.45	11	11.55	125	2.5	125	1	5	8.4	8.0	0.25	430
1N5349B	1N5349B	11.4	12	12.6	100	2.5	125	1	2	9.1	7.5	0.25	395
1N5350B	1N5350B	12.35	13	13.65	100	2.5	100	1	1	9.9	7.0	0.25	365
1N5351B	1N5351B	13.3	14	14.7	100	2.5	75	1	1	10.6	6.7	0.25	340
1N5352B	1N5352B	14.25	15	15.75	75	2.5	75	1	1	11.5	6.3	0.25	315
1N5353B	1N5353B	15.2	16	16.8	75	2.5	75	1	1	12.2	6.0	0.3	295
1N5354B	1N5354B	16.15	17	17.85	70	2.5	75	1	0.5	12.9	5.8	0.35	280
1N5355B	1N5355B	17.1	18	18.9	65	2.5	75	1	0.5	13.7	5.5	0.4	264
1N5356B	1N5356B	18.05	19	19.95	65	3	75	1	0.5	14.4	5.3	0.4	250
1N5357B	1N5357B	19	20	21	65	3	75	1	0.5	15.2	5.1	0.4	237
1N5358B	1N5358B	20.9	22	23.1	50	3.5	75	1	0.5	16.7	4.7	0.45	216
1N5359B	1N5359B	22.8	24	25.2	50	3.5	100	1	0.5	18.2	4.4	0.55	198
1N5360B	1N5360B	23.75	25	26.25	50	4	110	1	0.5	19	4.3	0.55	190
1N5361B*	1N5361B	25.65	27	28.35	50	5	120	1	0.5	20.6	4.1	0.6	176
1N5362B	1N5362B	26.6	28	29.4	50	6	130	1	0.5	21.2	3.9	0.6	170

1. TOLERANCE AND TYPE NUMBER DESIGNATION

The JEDEC type numbers shown indicate a tolerance of $\pm 5\%$.

2. ZENER VOLTAGE (V_Z) and IMPEDANCE (I_{ZT} and I_{ZK})

Test conditions for zener voltage and impedance are as follows: I_Z is applied 40 ± 10 ms prior to reading. Mounting contacts are located $3/8''$ to $1/2''$ from the inside edge of mounting clips to the body of the diode ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

3. SURGE CURRENT (I_R)

Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 5 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zener are shown in Figure 6. Mounting contact located as specified in Note 2 ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

4. VOLTAGE REGULATION (ΔV_Z)

The conditions for voltage regulation are as follows: V_Z measurements are made at 10% and then at 50% of the I_Z max value listed in the electrical characteristics table. The test current time duration for each V_Z measurement is 40 ± 10 ms. Mounting contact located as specified in Note 2 ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

5. MAXIMUM REGULATOR CURRENT (I_{ZM})

The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I_{ZM} for any device may not exceed the value of 5 watts divided by the actual V_Z of the device. $T_L = 75^\circ\text{C}$ at $3/8''$ maximum from the device body.

*Not Available in the 2000/Ammo Pack.

1N5333B Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.2\text{ V Max}$ @ $I_F = 1.0\text{ A}$ for all types)

Device (Note 6)	Device Marking	Zener Voltage (Note 7)				Zener Impedance (Note 7)			Leakage Current		I _R (Note 8)	ΔV _Z (Note 9)	I _{ZM} (Note 10)
		V _Z (Volts)			@ I _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} @ I _{ZK}	I _{ZK}	I _R @ V _R				
		Min	Nom	Max	mA	Ω	Ω	mA	μA Max	Volts			
1N5363B	1N5363B	28.5	30	31.5	40	8	140	1	0.5	22.8	3.7	0.6	158
1N5364B	1N5364B	31.35	33	34.65	40	10	150	1	0.5	25.1	3.5	0.6	144
1N5365B	1N5365B	34.2	36	37.8	30	11	160	1	0.5	27.4	3.5	0.65	132
1N5366B	1N5366B	37.05	39	40.95	30	14	170	1	0.5	29.7	3.1	0.65	122
1N5367B	1N5367B	40.85	43	45.15	30	20	190	1	0.5	32.7	2.8	0.7	110
1N5368B	1N5368B	44.65	47	49.35	25	25	210	1	0.5	35.8	2.7	0.8	100
1N5369B	1N5369B	48.45	51	53.55	25	27	230	1	0.5	38.8	2.5	0.9	93
1N5370B	1N5370B	53.2	56	58.8	20	35	280	1	0.5	42.6	2.3	1.0	86
1N5371B	1N5371B	57	60	63	20	40	350	1	0.5	45.5	2.2	1.2	79
1N5372B	1N5372B	58.9	62	65.1	20	42	400	1	0.5	47.1	2.1	1.35	76
1N5373B	1N5373B	64.6	68	71.4	20	44	500	1	0.5	51.7	2.0	1.52	70
1N5374B	1N5374B	71.25	75	78.75	20	45	620	1	0.5	56	1.9	1.6	63
1N5375B	1N5375B	77.9	82	86.1	15	65	720	1	0.5	62.2	1.8	1.8	58
1N5376B	1N5376B	82.65	87	91.35	15	75	760	1	0.5	66	1.7	2.0	54.5
1N5377B	1N5377B	86.45	91	95.55	15	75	760	1	0.5	69.2	1.6	2.2	52.5
1N5378B	1N5378B	95	100	105	12	90	800	1	0.5	76	1.5	2.5	47.5
1N5379B	1N5379B	104.5	110	115.5	12	125	1000	1	0.5	83.6	1.4	2.5	43
1N5380B	1N5380B	114	120	126	10	170	1150	1	0.5	91.2	1.3	2.5	39.5
1N5381B	1N5381B	123.5	130	136.5	10	190	1250	1	0.5	98.8	1.2	2.5	36.6
1N5382B	1N5382B	133	140	147	8	230	1500	1	0.5	106	1.2	2.5	34
1N5383B	1N5383B	142.5	150	157.5	8	330	1500	1	0.5	114	1.1	3.0	31.6
1N5384B	1N5384B	152	160	168	8	350	1650	1	0.5	122	1.1	3.0	29.4
1N5385B	1N5385B	161.5	170	178.5	8	380	1750	1	0.5	129	1.0	3.0	28
1N5386B	1N5386B	171	180	189	5	430	1750	1	0.5	137	1.0	4.0	26.4
1N5387B	1N5387B	180.5	190	199.5	5	450	1850	1	0.5	144	0.9	5.0	25
1N5388B	1N5388B	190	200	210	5	480	1850	1	0.5	152	0.9	5.0	23.6

6. TOLERANCE AND TYPE NUMBER DESIGNATION

The JEDEC type numbers shown indicate a tolerance of $\pm 5\%$.

7. ZENER VOLTAGE (V_Z) and IMPEDANCE (I_{ZT} and I_{ZK})

Test conditions for zener voltage and impedance are as follows: I_Z is applied 40 ± 10 ms prior to reading. Mounting contacts are located $3/8''$ to $1/2''$ from the inside edge of mounting clips to the body of the diode ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

8. SURGE CURRENT (I_R)

Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 5 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zener are shown in Figure 6. Mounting contact located as specified in Note 7 ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

9. VOLTAGE REGULATION (ΔV_Z)

The conditions for voltage regulation are as follows: V_Z measurements are made at 10% and then at 50% of the I_Z max value listed in the electrical characteristics table. The test current time duration for each V_Z measurement is 40 ± 10 ms. Mounting contact located as specified in Note 7 ($T_A = 25^\circ\text{C} + 8^\circ\text{C}, -2^\circ\text{C}$).

10. MAXIMUM REGULATOR CURRENT (I_{ZM})

The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I_{ZM} for any device may not exceed the value of 5 watts divided by the actual V_Z of the device. $T_L = 75^\circ\text{C}$ at $3/8''$ maximum from the device body.

1N5333B Series

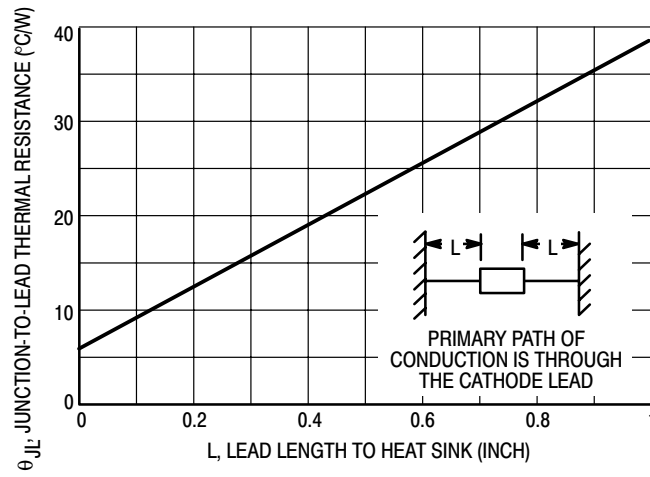


Figure 1. Typical Thermal Resistance

TEMPERATURE COEFFICIENTS

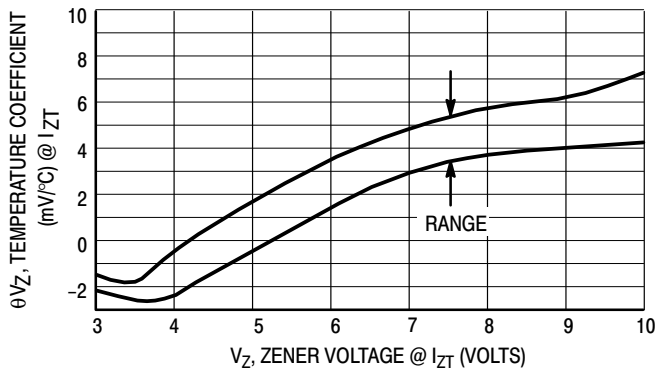


Figure 2. Temperature Coefficient-Range for Units 3 to 10 Volts

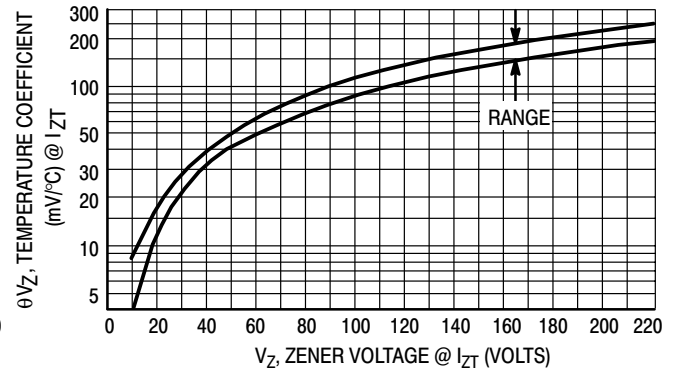


Figure 3. Temperature Coefficient-Range for Units 10 to 220 Volts

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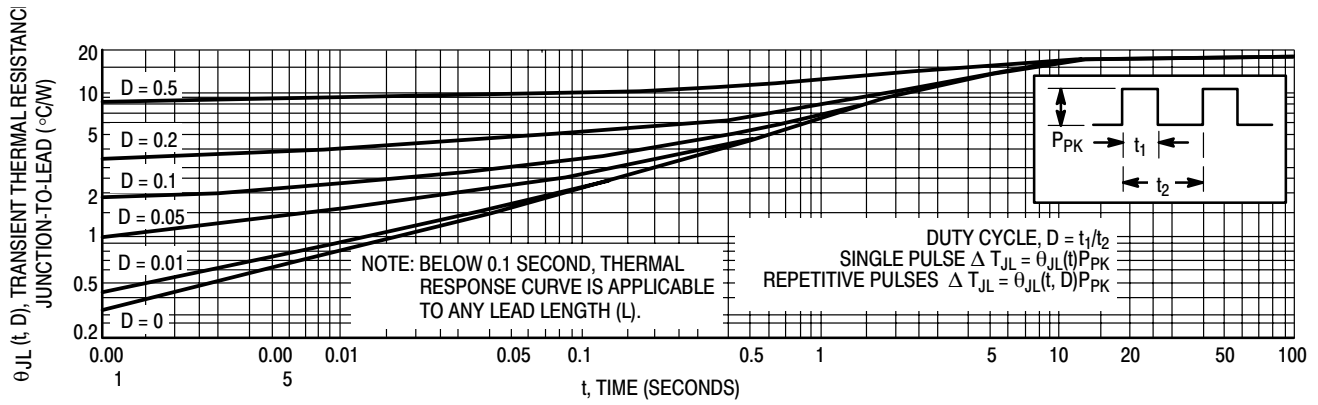


Figure 4. Typical Thermal Response
L, Lead Length = 3/8 Inch

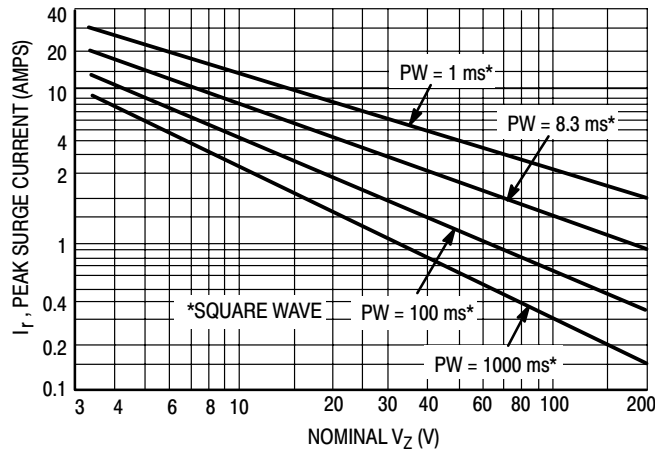


Figure 5. Maximum Non-Repetitive Surge Current
versus Nominal Zener Voltage
(See Note 3)

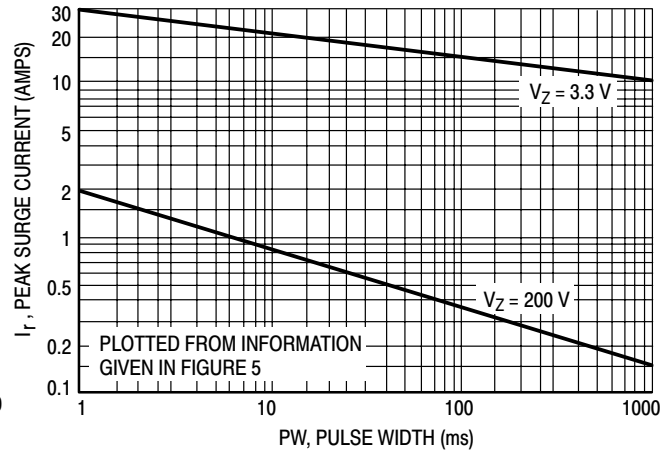


Figure 6. Peak Surge Current versus Pulse Width
(See Note 3)

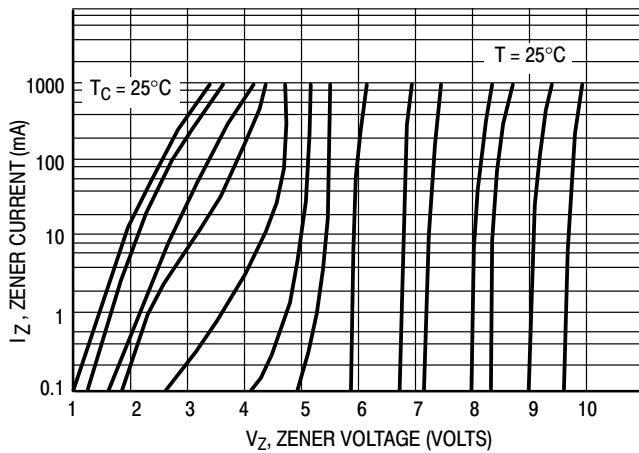


Figure 7. Zener Voltage versus Zener Current
 $V_Z = 3.3$ thru 10 Volts

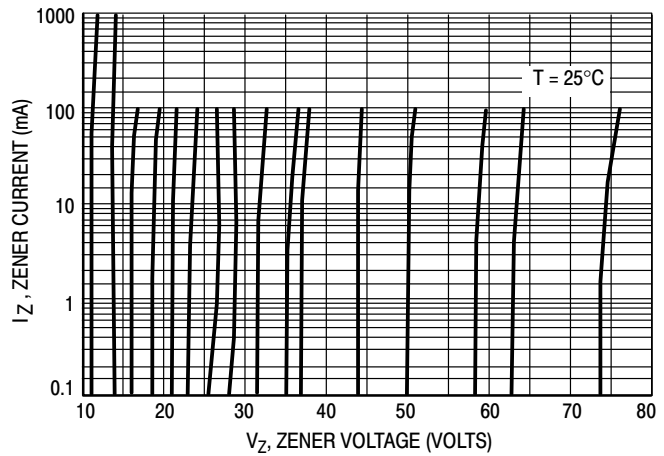


Figure 8. Zener Voltage versus Zener Current
 $V_Z = 11$ thru 75 Volts

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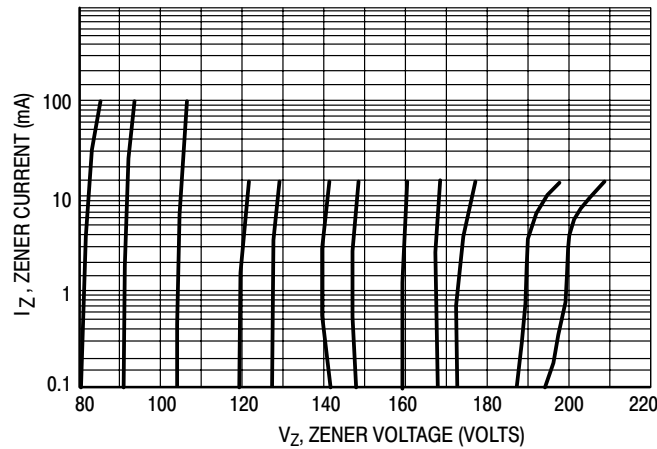


Figure 9. Zener Voltage versus Zener Current
 $V_Z = 82$ thru 200 Volts

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L , should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance and P_D is the power dissipation.

Junction Temperature, T_J , may be found from:

$$T_J = T_L + \Delta T_{JL}$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 4 for a train of power pulses or from Figure 1 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of T_J (ΔT_J) may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

θ_{VZ} , the zener voltage temperature coefficient, is found from Figures 2 and 3.

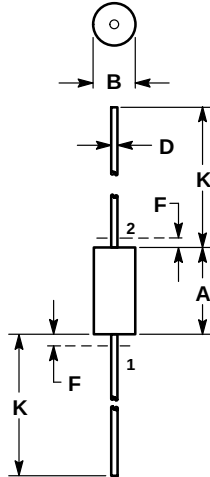
Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Data of Figure 4 should not be used to compute surge capability. Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 5 be exceeded.

1N5333B Series

PACKAGE DIMENSIONS

AXIAL LEAD CASE 17-02 ISSUE C



NOTES:

1. LEAD DIAMETER AND FINISH NOT CONTROLLED WITHIN DIMENSION F.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.330	0.350	8.38	8.89
B	0.130	0.145	3.30	3.68
D	0.037	0.043	0.94	1.09
F	---	0.050	---	1.27
K	1.000	1.250	25.40	31.75

STYLE 1:

- PIN 1. ANODE
- CATHODE

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